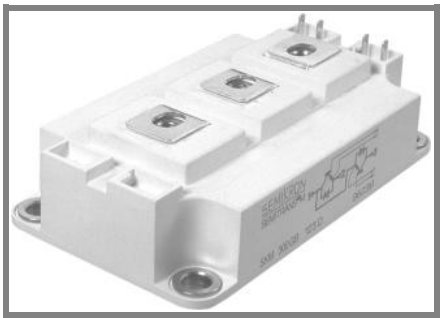
SKM 150GB128D



SEMITRANS® 3

SPT IGBT Modules

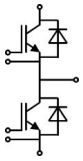
SKM 150GB128D

Features

- SPT = Soft punch-through technology
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_c

Typical Applications

- AC inverter drives
- UPS
- Electronic welders at f_{sw} up to 20 kHz

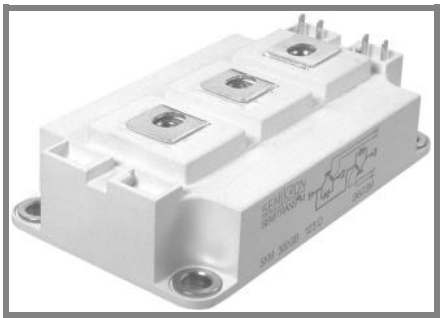


GB

Absolute Maximum Ratings	T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 150 °C	T_c = 25 °C	200	A
		T_c = 80 °C	140	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		200	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 600 V; $V_{GE} \leq$ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_{case} = 25 °C	150	A
		T_{case} = 80 °C	100	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		200	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	1100	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40... + 150	°C
T_{stg}			- 40... + 125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics	T_c = 25 °C, unless otherwise specified					
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 4 mA		4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,2	0,6	mA
V_{CE0}		T_j = 25 °C		1	1,15	V
		T_j = 125 °C		0,9	1,05	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		9	12	mΩ
		T_j = 125°C		12	15	mΩ
$V_{CE(sat)}$	I_{Cnom} = 100 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		1,9	2,35	V
		T_j = 125°C$_{chiplev.}$		2,1	2,55	V
C_{ies}				8,1		nF
C_{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		1,2		nF
C_{res}				1,1		nF
Q_G	V_{GE} = -8V - +20V			1200		nC
R_{Gint}	T_j = 25 °C			2,5		Ω
$t_{d(on)}$	R_{Gon} = 8 Ω	V_{CC} = 600V		80		ns
t_r		I_{Cnom}= 100A		40		ns
E_{on}		T_j = 125 °C		10		mJ
$t_{d(off)}$	R_{Goff} = 8 Ω	V_{GE} = ±15V		460		ns
t_f				65		ns
E_{off}				9		mJ
$R_{th(j-c)}$	per IGBT				0,15	K/W

SKM 150GB128D



SEMITRANS® 3

SPT IGBT Modules

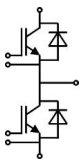
SKM 150GB128D

Features

- SPT = Soft punch-through technology
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_c

Typical Applications

- AC inverter drives
- UPS
- Electronic welders at f_{sw} up to 20 kHz

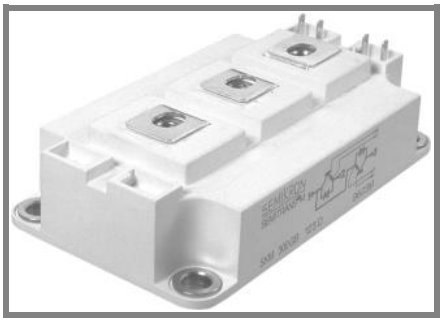


GB

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 100 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		2	2,5	V
		T_j = 125 °$C_{chiplev.}$		1,8	2,3	V
V_{F0}		T_j = 25 °C		1,1	1,45	V
		T_j = 125 °C			1,25	V
r_F		T_j = 25 °C		9	13	mΩ
		T_j = 125 °C			11	mΩ
I_{RRM}	I_{Fnom} = 100 A	T_j = 125 °C		145		A
Q_{rr}	di/dt = 3600 A/µs			16,5		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 600 V			5,5		mJ
$R_{th(j-c)D}$	per diode				0,3	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,35		mΩ
		T_{case}= 125 °C		0,5		mΩ
$R_{th(c-s)}$	per module				0,038	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M6		2,5		5	Nm
w					325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



SEMITRANS® 3

SPT IGBT Modules

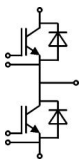
SKM 150GB128D

Features

- SPT = Soft punch-through technology
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_c

Typical Applications

- AC inverter drives
- UPS
- Electronic welders at f_{sw} up to 20 kHz



GB

Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	116	mk/W
R_i	i = 2	28	mk/W
R_i	i = 3	5,4	mk/W
R_i	i = 4	0,6	mk/W
tau_i	i = 1	0,0576	s
tau_i	i = 2	0,0073	s
tau_i	i = 3	0,023	s
tau_i	i = 4	0,02	s
$Z_{th(j-c)D}$			
R_i	i = 1	190	mk/W
R_i	i = 2	85	mk/W
R_i	i = 3	21,5	mk/W
R_i	i = 4	3,5	mk/W
tau_i	i = 1	0,0331	s
tau_i	i = 2	0,0113	s
tau_i	i = 3	0,0012	s
tau_i	i = 4	0,001	s

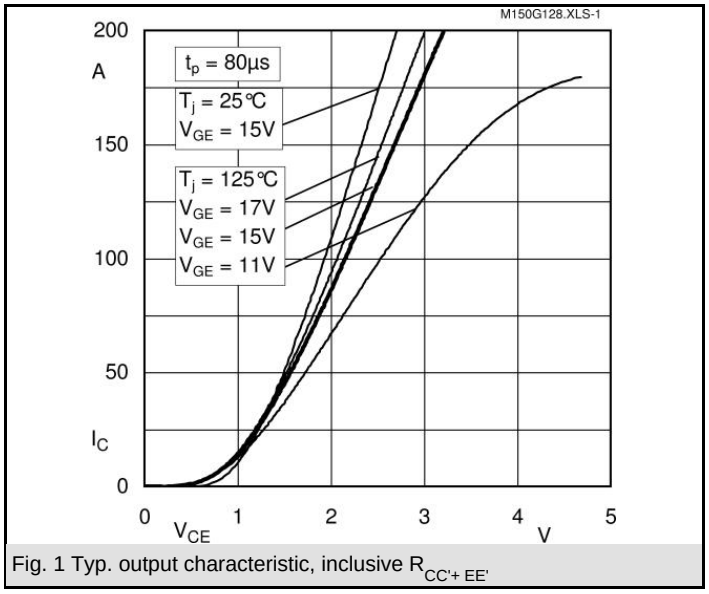


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

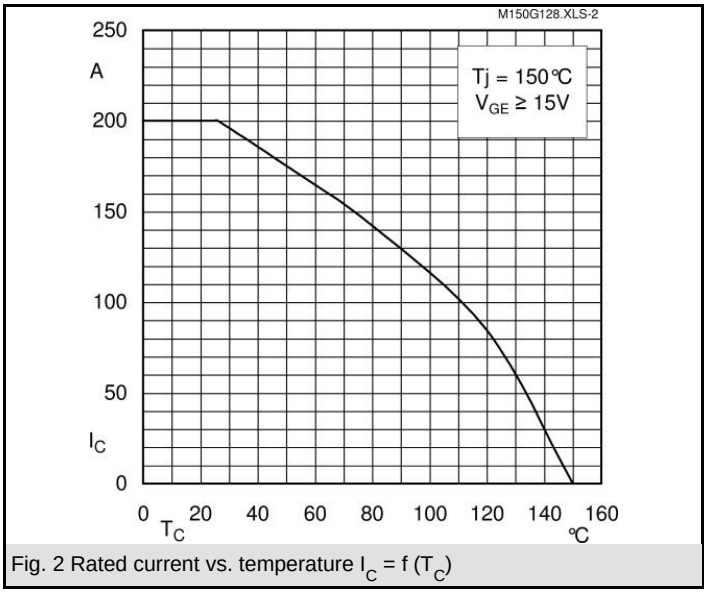


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

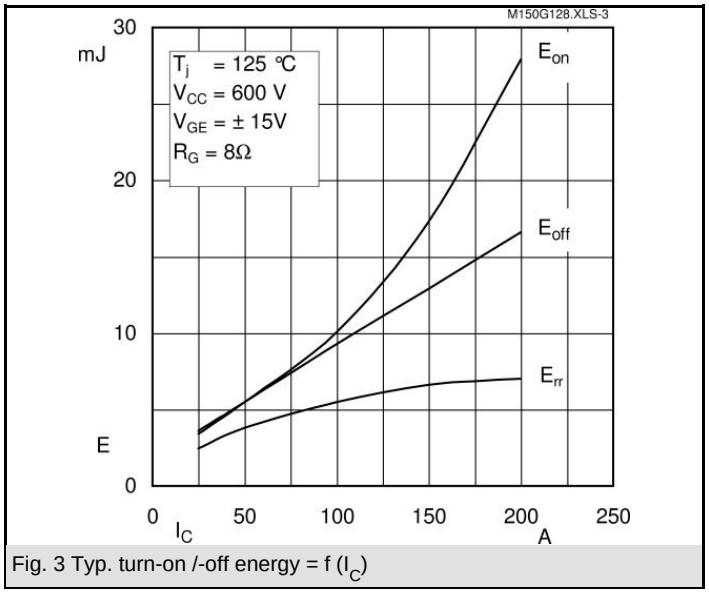


Fig. 3 Typ. turn-on /-off energy = f (I_C)

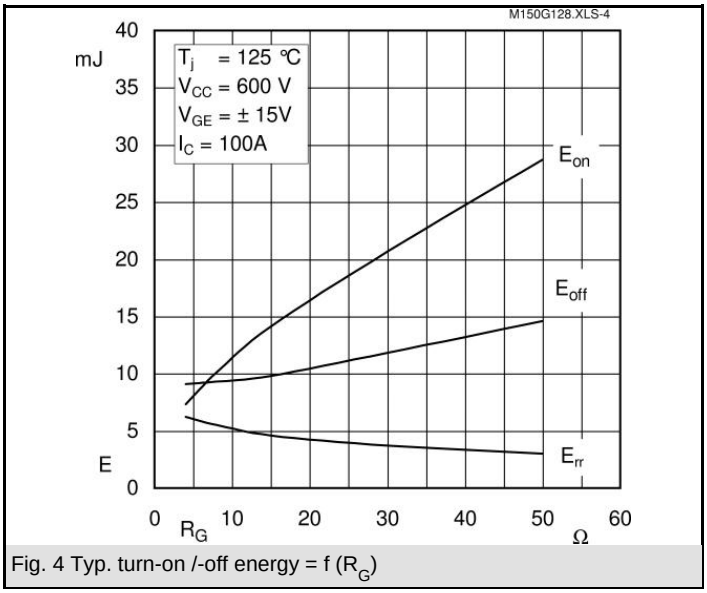


Fig. 4 Typ. turn-on /-off energy = f (R_G)

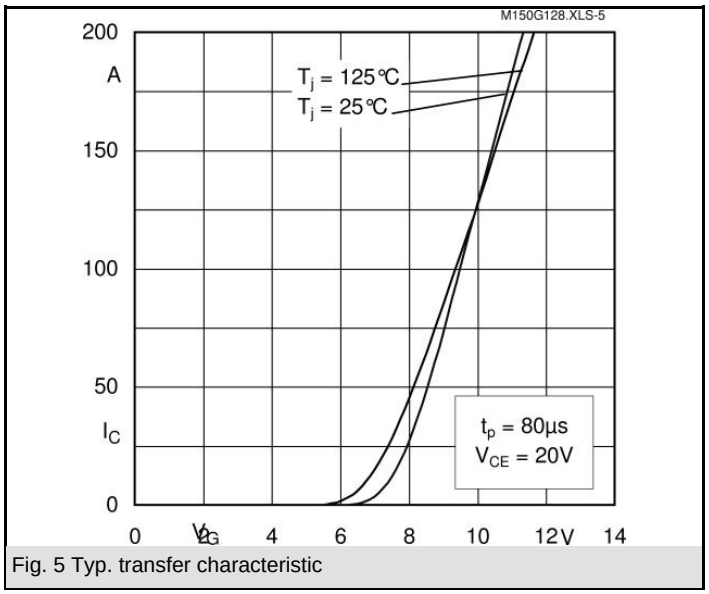


Fig. 5 Typ. transfer characteristic

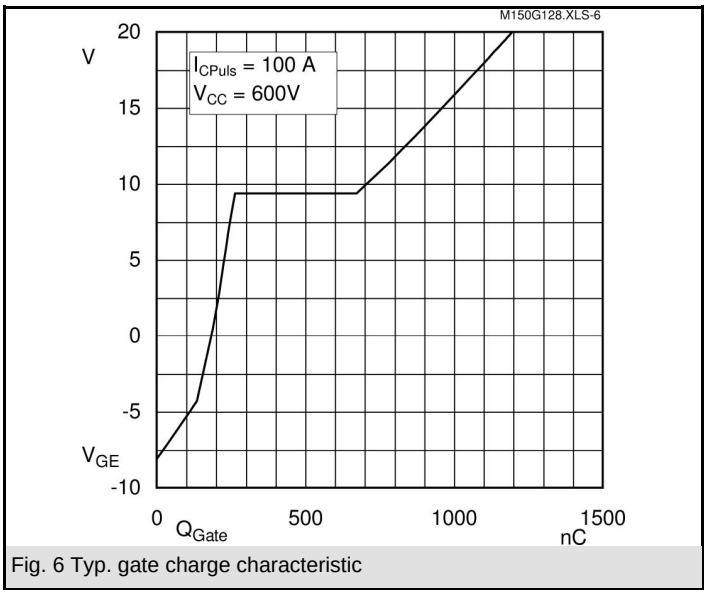


Fig. 6 Typ. gate charge characteristic

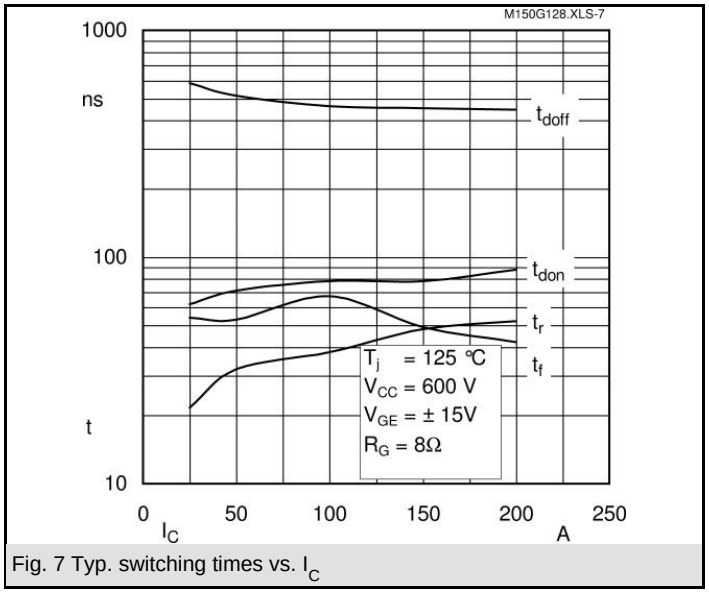


Fig. 7 Typ. switching times vs. I_C

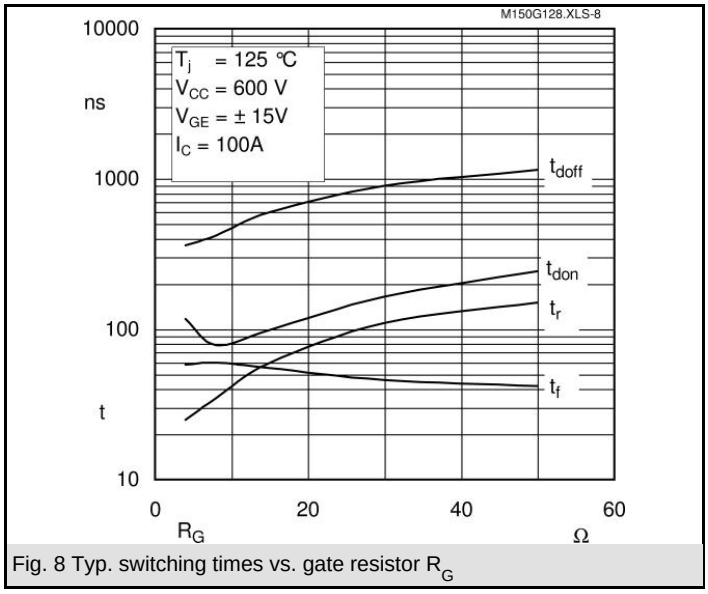


Fig. 8 Typ. switching times vs. gate resistor R_G

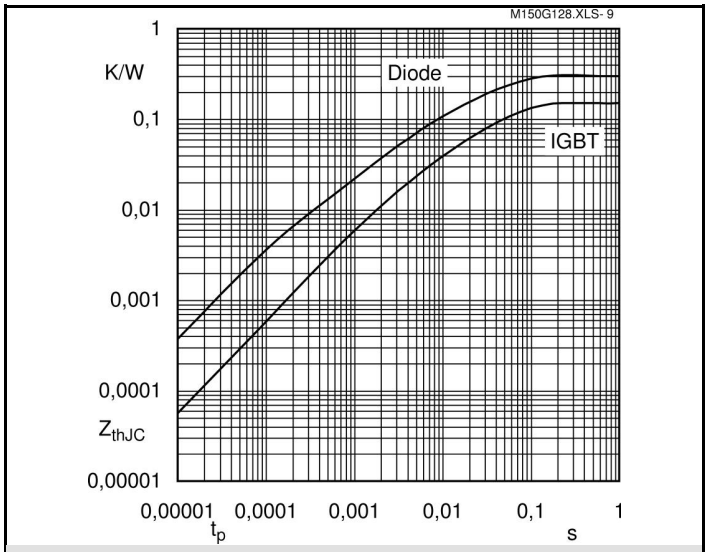


Fig. 9 Transient thermal impedance

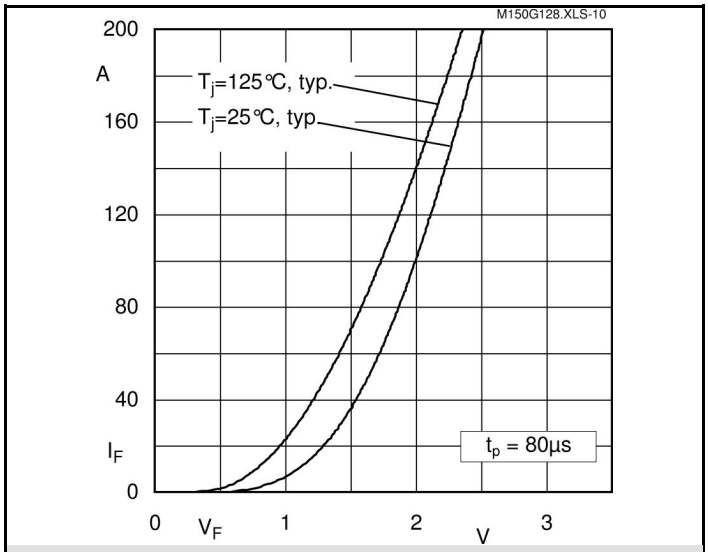


Fig. 10 CAL diode forward characteristic

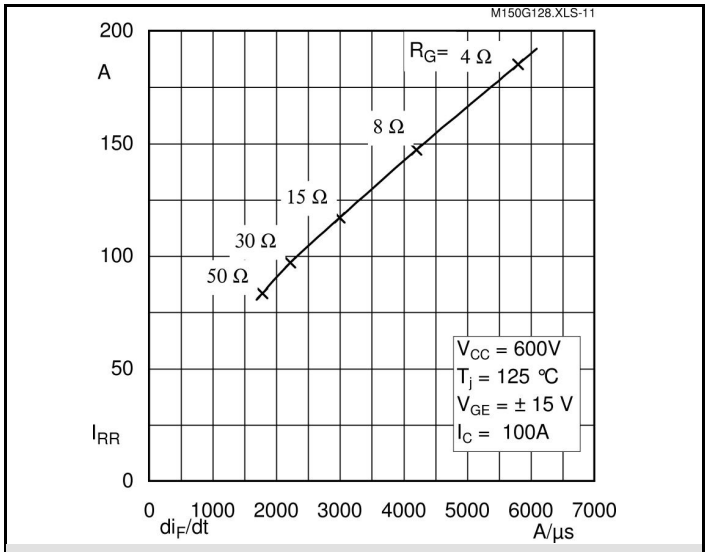


Fig. 11 Typ. CAL diode peak reverse recovery current

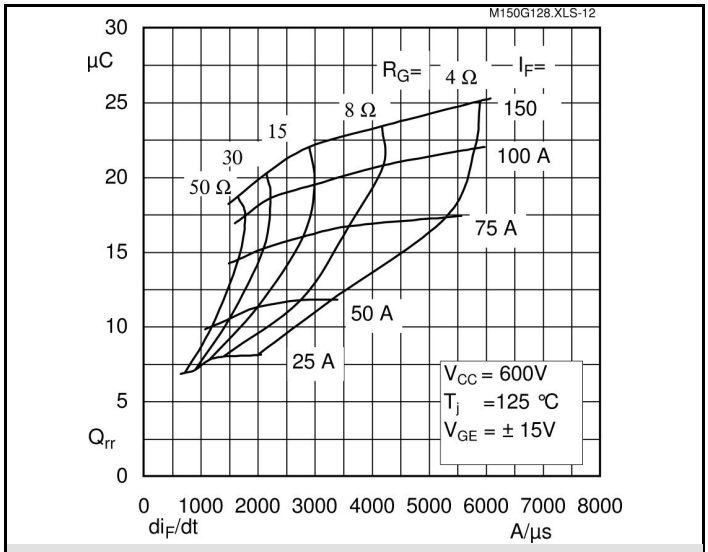
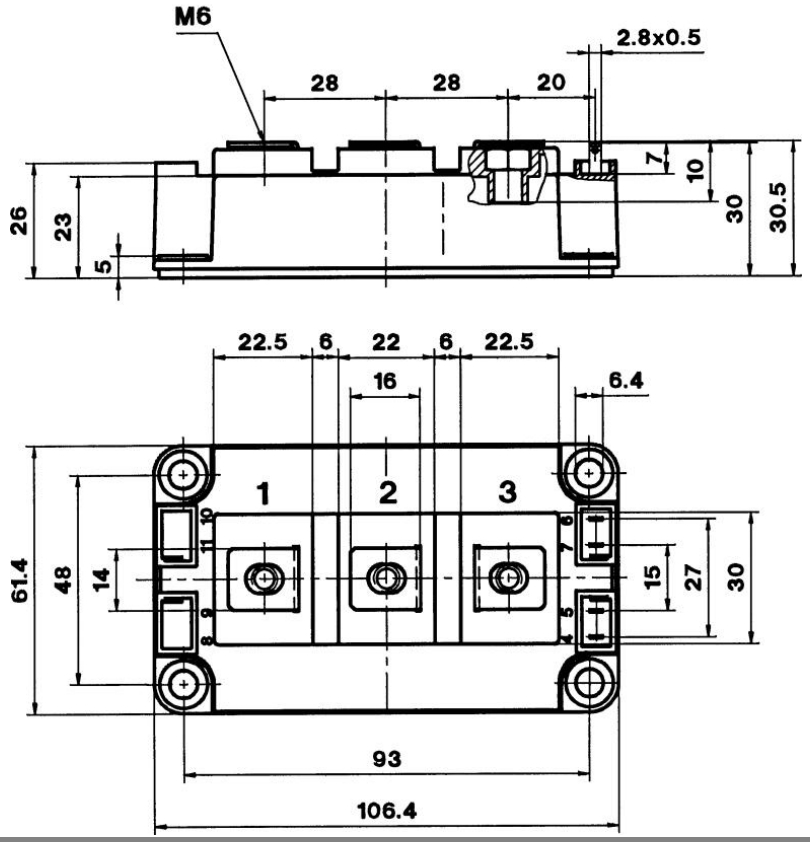


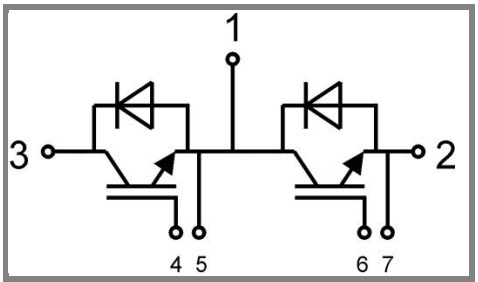
Fig. 12 Typ. CAL diode peak reverse recovery charge

UL Recognized File no. 63 532

CASED56



Case D 56



GB Case D 56

